

Fast Recovery rectifiers

Features

- Low profile package
- Ideal for automated placement
- Glass passivated chip junctions
- Fast switching for high efficiency
- High forward surge capability
- High temperature soldering:
260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC



SMA (DO - 214AC)

MARKING:RS1M

Mechanical Data

- Case:** JEDEC DO-214AC molded plastic body over glass passivated chip
- Terminals:** Solder plated, solderable per JESD22-B102
- Polarity:** Laser band denotes cathode end

Maximum Ratings & Thermal Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise noted)

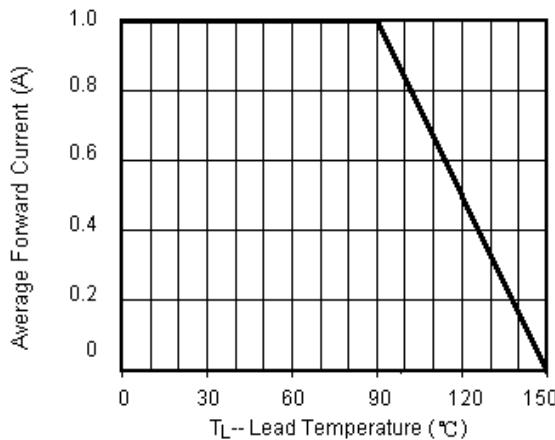
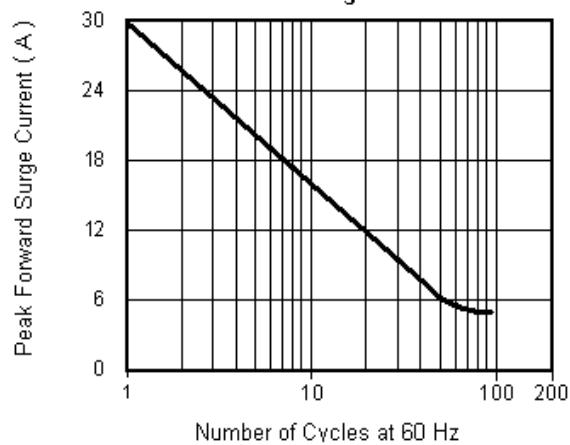
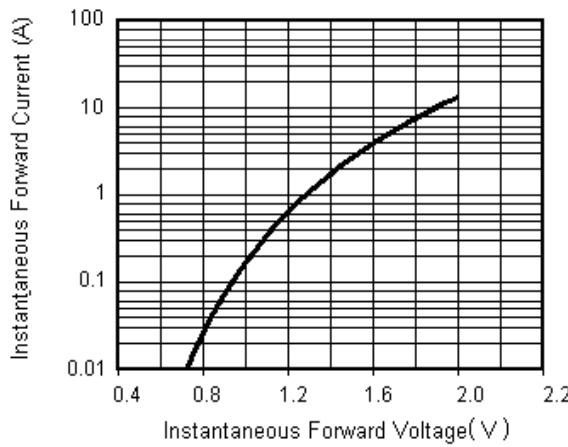
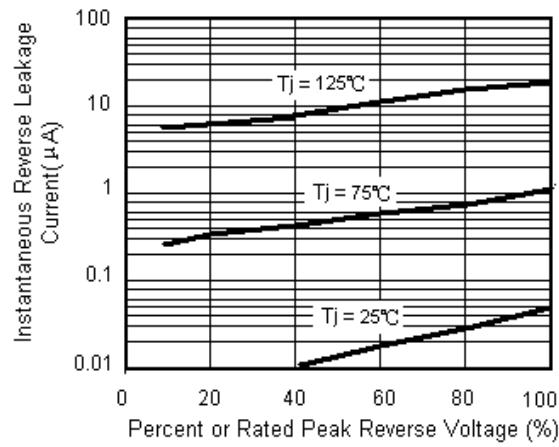
Items	Symbol	RS1M	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	1000	V
Maximum RMS voltage	V_{RMS}	700	V
Maximum DC blocking voltage	V_{DC}	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	1.0	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	30	A
Thermal resistance from junction to lead ⁽¹⁾	$R_{\theta JL}$	35	°C / W
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	°C

Note 1: Mounted on P.C.B. with 0.2 x 0.2" (5.0 x 5.0mm) copper pad areas.

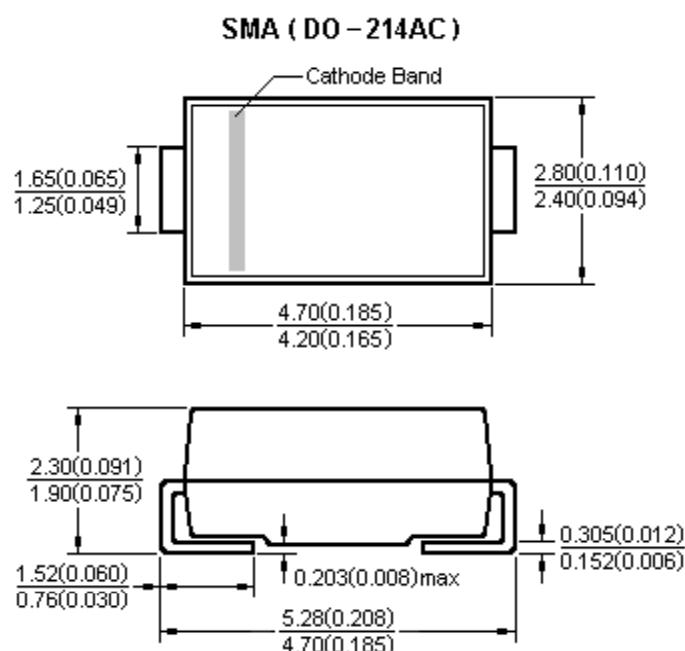
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Items	Test conditions	Symbol	RS1M	UNIT
Instantaneous forward voltage	$I_F=1.0\text{ A}^{(2)}$	V_F	1.3	V
Reverse current	$V_R=V_{DC}$	I_R	5	μA
			50	
Reverse recovery time	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	t_{rr}	500	nS
Typical junction capacitance	4.0 V ,1MHz	C_J	8	pF

Note 2: Pulse test:300μs pulse width,1% duty cycle.

Characteristic Curves ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)**Fig.1 Forward Current Derating Curve****Fig.2 Maximum Non-Repetitive Peak Forward Surge Current****Fig.3 Typical Instantaneous Forward Characteristics****Fig.4 Typical Reverse Leakage Characteristics**

Package Outline



Dimensions in millimeters and (inches)